onsemi

MC100LVEL05

Description

The MC100LVEL05 is a 2-input differential AND/NAND gate. The device is functionally equivalent to the MC100EL05 device and operates from a 3.3 V supply voltage. With propagation delays and output transition times equivalent to the EL05, the LVEL05 is ideally suited for those applications which require the ultimate in AC performance at low voltage power supplies.

Because a negative 2-input NAND is equivalent to a 2-input OR function, the differential inputs and outputs of the device allows the LVEL05 to also be used as a 2-input differential OR/NOR gate.

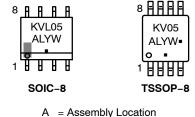
Features

- 340 ps Propagation Delay
- High Bandwidth Output Transitions
- ESD Protection:
 - > 4 kV Human Body Mode
 - ◆ > 200 V Machine Model
- The 100 Series Contains Temperature Compensation
- PECL Mode Operating Range: V_{CC} = 3.0 V to 3.8 V with V_{EE} = 0 V
- NECL Mode Operating Range: $V_{CC} = 0 V$ with $V_{EE} = -3.0 V$ to -3.8 V
- Internal Input Pulldown Resistors
- Q Output will Default LOW with All Inputs Open or at V_{EE}
- Meets or Exceeds JEDEC Spec EIA/JESD78 IC Latchup Test
- Moisture Sensitivity
 - ◆ Level 1 for SOIC-8
 - ◆ Level 3 for TSSOP-8
 - For Additional Information, see Application Note <u>AND8003/D</u>
- Flammability Rating: UL 94 V-0 @ 0.125 in, Oxygen Index: 28 to 34
- Transistor Count = 69 Devices
- These Devices are Pb-Free, Halogen Free and are RoHS Compliant





MARKING DIAGRAMS





- L = Wafer Lot Y = Year
- W = Work Week
- \overline{M} = Date Code
- = Pb-Free Package

(Note: Microdot may be in either location) *For additional marking information, refer to Application Note <u>AND8002/D</u>.

ORDERING INFORMATION

Device	Package	Shipping [†]
MC100LVEL05DG	SOIC-8 (Pb-Free)	98 Units/Tube
MC100LVEL05DR2G	SOIC-8 (Pb-Free)	2500/Tape & Reel
MC100LVEL05DTR2G	TSSOP-8 (Pb-Free)	2500/Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, <u>BRD8011/D</u>.

MC100LVEL05

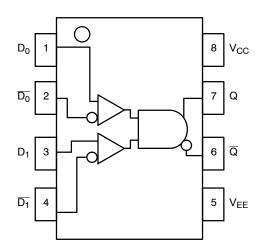


Figure 1. Logic Diagram and Pinout Assignment

Table 1. PIN DESCRIPTION

PIN	FUNCTION
D0, <u>D0</u> ; D1, <u>D1</u>	ECL Data Inputs
Q, <u>Q</u>	ECL Data Outputs
V _{CC}	Positive Supply
V _{EE}	Negative Supply

Table 2. MAXIMUM RATINGS

Symbol	Parameter	Condition 1	Condition 2	Rating	Unit
V _{CC}	PECL Mode Psower Supply	V _{EE} = 0 V		8 to 0	V
V_{EE}	NECL Mode Power Supply	$V_{CC} = 0 V$		-8 to 0	V
VI	PECL Mode Input Voltage NECL Mode Input Voltage	V _{EE} = 0 V V _{CC} = 0 V	$V_{I} \leq V_{CC}$ $V_{I} \geq V_{EE}$	6 to 0 -6 to 0	V
I _{out}	Output Current	Continuous Surge		50 100	mA
T _A	Operating Temperature Range			-40 to +85	°C
T _{stg}	Storage Temperature Range			-65 to +150	°C
θ_{JA}	Thermal Resistance (Junction-to-Ambient)	0 lfpm 500 lfpm	SOIC-8	190 130	°C/W
θ_{JC}	Thermal Resistance (Junction-to-Case)	Standard Board	SOIC-8	41 to 44 ±5%	°C/W
θ_{JA}	Thermal Resistance (Junction-to-Ambient)	0 lfpm 500 lfpm	TSSOP-8	185 140	°C/W
θ_{JC}	Thermal Resistance (Junction-to-Case)	Standard Board	TSSOP-8	41 to 44 ±5%	°C/W
T _{sol}	Wave Solder (Pb-Free)	< 2 to 3 sec @ 260°C		265	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

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			−40°C		25°C		85°C				
Symbol	Characteristic	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
I _{EE}	Power Supply Current		18	25		18	25		19	26	mA
V _{OH}	Output HIGH Voltage (Note 2)	2215	2295	2420	2275	2345	2420	2275	2345	2420	mV
V _{OL}	Output LOW Voltage (Note 2)	1470	1605	1745	1490	1595	1680	1490	1595	1680	mV
V _{IH}	Input HIGH Voltage (Single-Ended)	2135		2420	2135		2420	2135		2420	mV
V _{IL}	Input LOW Voltage (Single-Ended)	1490		1825	1490		1825	1490		1825	mV
VIHCMR	Input HIGH Voltage Common Mode Range (Differential) (Note 3) Vpp < 500 mV Vpp ≥ 500 mV	1.2 1.5		2.9 2.9	1.1 1.4		2.9 2.9	1.1 1.4		2.9 2.9	V
I _{IH}	Input HIGH Current			150			150			150	μA
IIL	Input LOW Current	0.5			0.5			0.5			μA

Table 3. LVPECL DC CHARACTERISTICS (V_{CC} = 3.3 V; V_{EF} = 0.0 V (Note 1))

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm.

1. Input and output parameters vary 1:1 with V_{CC}. V_{EE} can vary ± 0.3 V.

Outputs are terminated through a 50 ohm resistor to V_{CC} - 2.0 V.
V_{IHCMR} min varies 1:1 with V_{EE}, max varies 1:1 with V_{CC}. The V_{IHCMR} range is referenced to the most positive side of the differential input signal. Normal operation is obtained if the HIGH level falls within the specified range and the peak-to-peak voltage lies between V_{PP}min and 1 V.

			−40°C		25°C		85°C				
Symbol	Characteristic	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
I_{EE}	Power Supply Current		18	25		18	25		19	26	mA
V _{OH}	Output HIGH Voltage (Note 2)	-1085	-1005	-880	-1025	-955	-880	-1025	-955	-880	mV
V _{OL}	Output LOW Voltage (Note 2)	-1830	-1695	-1555	-1810	-1705	-1620	-1810	-1705	-1620	mV
VIH	Input HIGH Voltage (Single-Ended)	-1165		-880	-1165		-880	-1165		-880	mV
V _{IL}	Input LOW Voltage (Single-Ended)	-1810		-1475	-1810		-1475	-1810		-1475	mV
VIHCMR	Input HIGH Voltage Common Mode Range (Differential) (Note 3) Vpp < 500 mV Vpp ≥ 500 mV	-2.1 -1.8		-0.4 -0.4	-2.2 -1.9		-0.4 -0.4	-2.2 -1.9		-0.4 -0.4	V
I _{IH}	Input HIGH Current			150			150			150	μA
IIL	Input LOW Current	0.5			0.5			0.5			μA

Table 4. LVNECL DC CHARACTERISTICS (V_{CC} = 0.0 V; V_{EE} = -3.3 V (Note 1))

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm.

1. Input and output parameters vary 1:1 with V_{CC}. V_{EE} can vary \pm 0.3 V. 2. Outputs are terminated through a 50 ohm resistor to V_{CC} – 2.0 V.

V_{IHCMR} min varies 1:1 with V_{EE}, max varies 1:1 with V_{CC}. The V_{IHCMR} range is referenced to the most positive side of the differential input signal. Normal operation is obtained if the HIGH level falls within the specified range and the peak-to-peak voltage lies between V_{PP}min and 1 V.

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Table 5. AC CHARACTERISTICS	(V _{CC} = 3.3 V; V _{EE}	$= 0.0 \text{ V or V}_{CC} = 0.0 \text{ V}; \text{ V}_{B}$	_{EE} = -3.3 V (Note 1))
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		-40°C		25°C		85°C					
Symbol	Characteristic	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
f _{max}	Maximum Toggle Frequency		1.6			1.6			1.6		GHz
t _{PLH} t _{PHL}	Propagation Delay to Output	240	260	440	240	340	440	250		450	ps
t _{JITTER}	Cycle-to-Cycle Jitter		6.7			7.5			8.2		ps
V _{PP}	Input Swing (Note 2)	150		1000	150		1000	150		1000	mV
t _r t _f	Output Rise/Fall Times Q (20% – 80%)	100		320	100	210	320	100		320	ps

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm.

1. V_{EE} can vary ±0.3 V.

2. V_{PP}⁻(min) is the minimum input swing for which AC parameters are guaranteed. The device has a DC gain of ≈40.

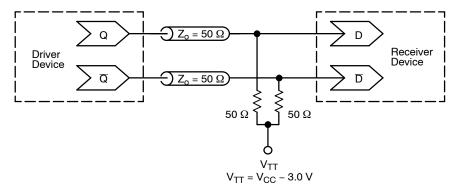


Figure 2. Typical Termination for Output Driver and Device Evaluation (See Application Note <u>AND8020/D</u> – Termination of ECL Logic Devices.)

Resource Reference of Application Notes

- AN1405/D ECL Clock Distribution Techniques
- AN1406/D Designing with PECL (ECL at +5.0 V)
- AN1503/D ECLinPS™ I/O SPiCE Modeling Kit
- AN1504/D Metastability and the ECLinPS Family
- AN1568/D Interfacing Between LVDS and ECL
- AN1672/D The ECL Translator Guide
- AND8001/D Odd Number Counters Design
- AND8002/D Marking and Date Codes
- AND8020/D Termination of ECL Logic Devices
- AND8066/D Interfacing with ECLinPS
- AND8090/D AC Characteristics of ECL Devices

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*For additional information on our Pb-Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

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STYLE 1: PIN 1. EMITTER COLLECTOR 2. COLLECTOR 3. 4. EMITTER 5. EMITTER BASE 6. 7 BASE EMITTER 8. STYLE 5: PIN 1. DRAIN 2. DRAIN З. DRAIN DRAIN 4. GATE 5. 6. GATE SOURCE 7. 8. SOURCE STYLE 9: PIN 1. EMITTER, COMMON COLLECTOR, DIE #1 COLLECTOR, DIE #2 2. З. EMITTER, COMMON 4. 5. EMITTER, COMMON 6 BASE. DIE #2 BASE, DIE #1 7. 8. EMITTER, COMMON STYLE 13: PIN 1. N.C. 2. SOURCE 3 GATE 4. 5. DRAIN 6. DRAIN DRAIN 7. 8. DRAIN STYLE 17: PIN 1. VCC 2. V2OUT V10UT З. TXE 4. 5. RXE 6. VFF 7. GND 8. ACC STYLE 21: PIN 1. CATHODE 1 2. CATHODE 2 3 CATHODE 3 CATHODE 4 4. 5. CATHODE 5 6. COMMON ANODE COMMON ANODE 7. 8. CATHODE 6 STYLE 25: PIN 1. VIN 2 N/C REXT З. 4. GND 5. IOUT 6. IOUT IOUT 7. 8. IOUT STYLE 29: BASE, DIE #1 PIN 1. 2 EMITTER, #1 BASE, #2 З. EMITTER, #2 4. 5 COLLECTOR, #2 COLLECTOR, #2 6.

STYLE 2: PIN 1. COLLECTOR, DIE, #1 2. COLLECTOR, #1 COLLECTOR, #2 3. 4 COLLECTOR, #2 BASE, #2 5. EMITTER, #2 6. 7 BASE #1 EMITTER, #1 8. STYLE 6: PIN 1. SOURCE 2. DRAIN 3. DRAIN SOURCE 4. SOURCE 5. 6. GATE GATE 7. 8. SOURCE STYLE 10: GROUND PIN 1. BIAS 1 OUTPUT 2. З. GROUND 4. 5. GROUND 6 BIAS 2 INPUT 7. 8. GROUND STYLE 14: PIN 1. N-SOURCE 2. N-GATE 3 P-SOURCE P-GATE 4. P-DRAIN 5 6. P-DRAIN N-DRAIN 7. N-DRAIN 8. STYLE 18: PIN 1. ANODE ANODE 2. SOURCE 3. GATE 4. 5. DRAIN 6 DRAIN CATHODE 7. 8. CATHODE STYLE 22: PIN 1. I/O LINE 1 2. COMMON CATHODE/VCC 3 COMMON CATHODE/VCC 4. I/O LINE 3 COMMON ANODE/GND 5. 6. I/O LINE 4 7. I/O LINE 5 8. COMMON ANODE/GND STYLE 26: PIN 1. GND 2 dv/dt З. ENABLE 4. ILIMIT 5. SOURCE SOURCE 6. SOURCE 7. 8. VCC STYLE 30: DRAIN 1 PIN 1. DRAIN 1 2 GATE 2 З. SOURCE 2 4. SOURCE 1/DRAIN 2 SOURCE 1/DRAIN 2 5. 6.

STYLE 3: PIN 1. DRAIN, DIE #1 DRAIN, #1 2. DRAIN, #2 З. DRAIN, #2 4. GATE, #2 5. SOURCE, #2 6. 7 GATE #1 8. SOURCE, #1 STYLE 7: PIN 1. INPUT 2. EXTERNAL BYPASS THIRD STAGE SOURCE GROUND З. 4. 5. DRAIN 6. GATE 3 SECOND STAGE Vd 7. FIRST STAGE Vd 8. STYLE 11: PIN 1. SOURCE 1 GATE 1 SOURCE 2 2. 3. GATE 2 4. 5. DRAIN 2 6. DRAIN 2 DRAIN 1 7. 8. DRAIN 1 STYLE 15: PIN 1. ANODE 1 2. ANODE 1 ANODE 1 3 ANODE 1 4. 5. CATHODE, COMMON CATHODE, COMMON CATHODE, COMMON 6. 7. CATHODE, COMMON 8. STYLE 19: PIN 1. SOURCE 1 GATE 1 SOURCE 2 2. 3. GATE 2 4. 5. DRAIN 2 6. MIRROR 2 7. DRAIN 1 8. **MIRROR 1** STYLE 23: PIN 1. LINE 1 IN COMMON ANODE/GND COMMON ANODE/GND 2. 3 LINE 2 IN 4. LINE 2 OUT 5. COMMON ANODE/GND COMMON ANODE/GND 6. 7. 8. LINE 1 OUT STYLE 27: PIN 1. ILIMIT 2 OVI 0 UVLO З. 4. INPUT+ 5. 6. SOURCE SOURCE SOURCE 7. 8 DRAIN

STYLE 4: PIN 1. 2. ANODE ANODE ANODE З. 4. ANODE ANODE 5. 6. ANODE 7 ANODE COMMON CATHODE 8. STYLE 8: PIN 1. COLLECTOR, DIE #1 2. BASE, #1 BASE #2 З. COLLECTOR, #2 4. COLLECTOR, #2 5. 6. EMITTER, #2 EMITTER, #1 7. 8. COLLECTOR, #1 STYLE 12: PIN 1. SOURCE SOURCE 2. 3. GATE 4. 5. DRAIN 6. DRAIN DRAIN 7. 8. DRAIN STYLE 16 EMITTER, DIE #1 PIN 1. 2. BASE, DIE #1 EMITTER, DIE #2 3 BASE, DIE #2 4. 5. COLLECTOR, DIE #2 6. COLLECTOR, DIE #2 COLLECTOR, DIE #1 7. COLLECTOR, DIE #1 8. STYLE 20: PIN 1. SOURCE (N) GATE (N) SOURCE (P) 2. 3. 4. GATE (P) 5. DRAIN 6. DRAIN DRAIN 7. 8. DRAIN STYLE 24: PIN 1. BASE EMITTER 2. 3 COLLECTOR/ANODE COLLECTOR/ANODE 4. 5. CATHODE

6. CATHODE COLLECTOR/ANODE 7. 8. COLLECTOR/ANODE STYLE 28: PIN 1. SW_TO_GND 2. DASIC OFF DASIC_SW_DET З. 4. GND 5. 6. V MON VBULK 7. VBULK

7. VOULK 8. VIN

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SOURCE 1/DRAIN 2

7.

8. GATE 1

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7.

8

COLLECTOR, #1

COLLECTOR, #1

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-T- SEATING

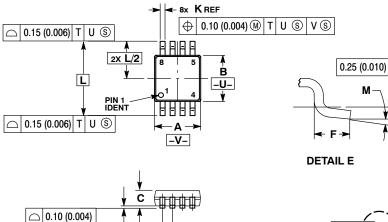
PLANE

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TSSOP-8 3.00x3.00x0.95 CASE 948R-02 ISSUE A

DATE 07 APR 2000



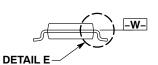
0.25 (0.010)

NOTES:

4.

5.

PER SIDE.



	MILLIN	IETERS	INCHES				
DIM	MIN	MAX	MIN	MAX			
Α	2.90	3.10	0.114	0.122			
В	2.90	3.10	0.114	0.122			
С	0.80	1.10	0.031	0.043			
D	0.05	0.15	0.002	0.006			
F	0.40	0.70	0.016	0.028			
G	0.65	BSC	0.026 BSC				
K	0.25	0.40	0.010	0.016			
L	4.90	BSC	0.193 BSC				
М	0°	6 °	0°	6 °			

NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: MILLIMETER. 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH. PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE. 4. DIMENSION B DOES NOT INCLUDE INTERLED

FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010)

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